

# ZXTP25040DFL 40V, SOT23, PNP low power transistor

## **Summary**

 $BV_{CEO} > -40V$ 

 $BV_{ECO} > -3V$ 

 $I_{C(cont)} = -1.5A$ 

V<sub>CE(sat)</sub> < -115mV @ 1A

 $R_{CE(sat)} = 82m\Omega$ 

 $P_{D} = 350 \text{mW}$ 

Complementary part number ZXTN25040DFL



Advanced process capability has been used to achieve high current gain hold up making this device ideal for applications requiring high pulse currents.

### **Features**

- · High peak current
- · Low saturation voltage
- · 40V forward blocking voltage

### **Applications**

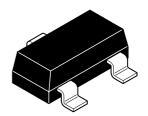
- · MOSFET and IGBT gate driving
- · Low power DC-DC conversion

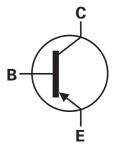
### **Ordering information**

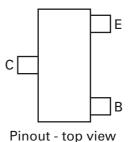
Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP25040DFLTA	7	8	3,000

# Device marking

1A2







# **Absolute maximum ratings**

Parameter	Symbol	Limit	Unit
Collector-base voltage	V <sub>CBO</sub>	-45	V
Collector-emitter voltage (forward blocking)	V <sub>CEO</sub>	-40	V
Emitter-collector voltage (reverse blocking)	V <sub>ECO</sub>	-3	V
Emitter-base voltage	V <sub>EBO</sub>	-7	V
Continuous collector current <sup>(a)</sup>	I <sub>C</sub>	-1.5	Α
Base current	I <sub>B</sub>	-0.5	Α
Peak pulse current	I <sub>CM</sub>	-5	Α
Power dissipation at T <sub>amb</sub> =25°C <sup>(a)</sup>	P <sub>D</sub>	350	mW
Linear derating factor		2.8	mW/°C
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C

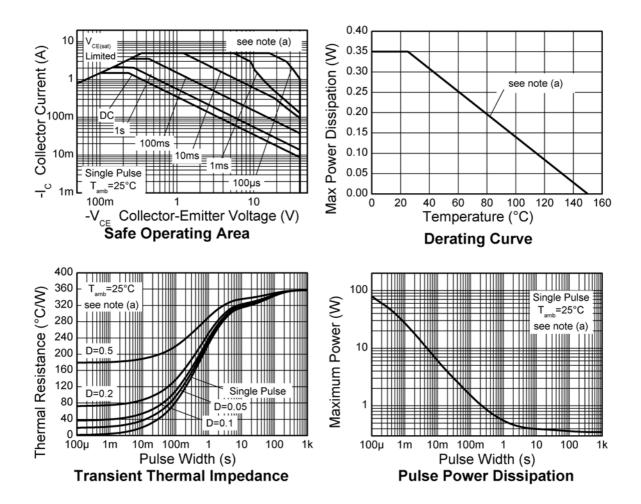
## Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	357	°C/W

### NOTES:

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

### **Characteristics**



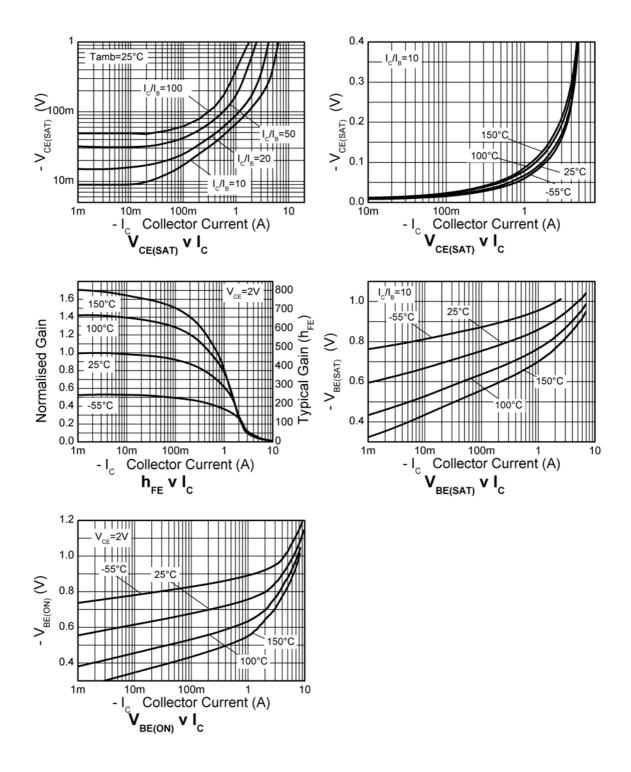
# Electrical characteristics (at T<sub>amb</sub> = 25°C unless otherwise stated)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CBO</sub>	-45	-75		V	$I_C = -100 \mu A$
Collector-emitter breakdown voltage (base open)	BV <sub>CEO</sub>	-40	-65		V	I <sub>C</sub> = -10mA <sup>(*)</sup>
Emitter-collector breakdown voltage (reverse blocking)	BV <sub>ECO</sub>	-3	-8.7		V	$I_E = -100 \mu A^{(*)}$
Emitter-base breakdown voltage	BV <sub>EBO</sub>	-7	-8.2		٧	$I_E = -100 \mu A$
Collector cut-off current	I <sub>CBO</sub>		<-1	-50 -20	nA μA	$V_{CB} = -36V$ $V_{CB} = -36V$ , $T_{amb} = 100$ °C
Emitter cut-off current	I <sub>EBO</sub>		<-1	-50	nA	V <sub>EB</sub> = -5.6V
Collector-emitter saturation	V <sub>CE(sat)</sub>		-75	-95	mV	$I_C = -0.5A$ , $I_B = -20mA^{(*)}$
voltage			-200	-290	mV	$I_C = -1A$ , $I_B = -20 \text{mA}^{(*)}$
			-95	-115		$I_C = -1A$ , $I_B = -100 \text{mA}^{(*)}$
			-160	-190	mV	$I_C = -1.5A$ , $I_B = -75mA^{(*)}$
			-245	-300	mV	$I_C = -3A$ , $I_B = -300 \text{mA}^{(*)}$
Base-emitter saturation voltage	V <sub>BE(sat)</sub>		-915	-1000	mV	$I_C = -1.5A$ , $I_B = -75mA^{(*)}$
Base-emitter turn-on voltage	V <sub>BE(on)</sub>		-825	-900	mV	$I_C = -1.5A$ , $V_{CE} = -2V^{(*)}$
Static forward current transfer ratio	h <sub>FE</sub>	300	450	900		I <sub>C</sub> = -10mA, V <sub>CE</sub> = -2V <sup>(*)</sup>
ratio		120	200			$I_C = -1.5A$ , $V_{CE} = -2V^{(*)}$
		15	40			$I_C = -3A$ , $V_{CE} = -2V^{(*)}$
Transition frequency	f <sub>T</sub>		270		MHz	I <sub>C</sub> = -50mA, V <sub>CE</sub> = -10V f = 50MHz
Output capacitance	C <sub>obo</sub>		17.4	25	pF	V <sub>CB</sub> = -10V, f = 1MHz <sup>(*)</sup>
Delay time	t <sub>(d)</sub>		34		ns	$V_{CC} = -15V. I_{C} = -750mA,$
Rise time	t <sub>(r)</sub>		41		ns	$I_{B1} = I_{B2} = -15 \text{mA}.$
Storage time	t <sub>(s)</sub>		266		ns	
Fall time	t <sub>(f)</sub>		53		ns	

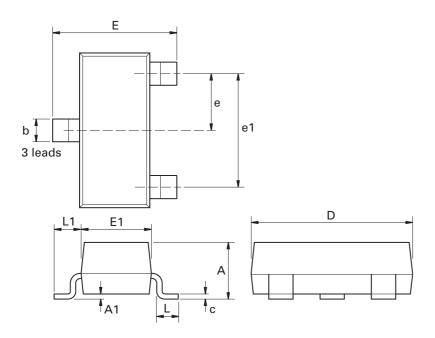
#### NOTES:

(\*) Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu s$ ; duty cycle  $\leq$  2%.

# **Typical characteristics**



# Package outline - SOT23



Dim.	Millim	limeters I		hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.	1	Min.	Max.	Max.	Max.
Α	2.67	3.05	0.105	0.120	Н	0.33	0.51	0.013	0.020
В	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
С	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	М	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 N	ЮM	0.0375	NOM
G	1.90	NOM	0.075	NOM	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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